Defining the Value of Injection Current and Effective Electrical Contact Area for EGaIn-Based Molecular Tunneling Junctions

Felice C. Simeone, Hyo Jae Yoon, Martin M. Thuo, Jabulani R. Barber, Barbara Smith, and George M. Whitesides*

Department of Chemistry and Chemical Biology, Harvard University, Cambridge, Massachusetts 02138, United States

Supporting Information

ABSTRACT: Analysis of rates of tunneling across self-assembled monolayers (SAMs) of n-alkanethiolates Scn with n = number of carbon atoms incorporated in junctions having structure Ag75-SAM//Ga2O3/EGaIn leads to a value for the injection tunnel current density J0 (i.e., the current flowing through an ideal junction with n = 0) of 10−3 to 10−2 A cm−2 (V = +0.5 V). This estimation of J0 does not involve an extrapolation in length, because it was possible to measure current densities across SAMs over the range of lengths n = 1−18. This value of J0 is estimated under the assumption that values of the geometrical contact area equal the values of the effective electrical contact area. Detailed experimental analysis, however, indicates that the roughness of the Ga2O3 layer, and that of the Ag75-SAM, determine values of the effective electrical contact area that are ∼10−4 the corresponding values of the geometrical contact area. Conversion of the values of geometrical contact area into the corresponding values of effective electrical contact area results in J0(+0.5 V) = 10−3 to 10−2 A cm−2, which is compatible with values reported for junctions using top-electrodes of evaporated Au, and graphene, and also comparable with values of J0 estimated from tunneling through single molecules. For these EGaIn-based junctions, the value of the tunneling decay factor β (β = 0.75 ± 0.02 Å−1; β = 0.92 ± 0.02 nC−1) falls within the consensus range across different types of junctions (β = 0.73−0.89 Å−1; β = 0.9−1.1 nC−1). A comparison of the characteristics of conical Ga2O3/EGaIn tips with the characteristics of other top-electrodes suggests that the EGaIn-based electrodes provide a particularly attractive technology for physical-organic studies of charge transport across SAMs.

INTRODUCTION

Measurements, using a number of techniques, of rates of charge transport by tunneling across self-assembled monolayers (SAMs) of n-alkanethiolates on silver and gold substrates show an interesting, puzzling, and unresolved mixture of consistency and inconsistency. Rates of tunneling across these SAMs follow the simplified Simmons equation,

\[ J(V) = J_0(V) \times 10^{-\beta d/2.303} \]  

(1)

with the falloff in current density J(V) (A cm−2) with increasing length d of the n-alkyl group giving (for even-numbered carbon chains, and at voltages in the range V = ±0.5 V) approximately the same value of the tunneling decay factor β by most or all methods of measurement (β = 0.73−0.89 Å−1; for d = nC = number of carbon atoms, β = 0.90−1.1 nC−1). Using mercury drops as top-electrodes, measurements of rates of tunneling across n-alkanes anchored to heavily doped silicon surfaces led to β = 0.9 ± 0.2 nC−1, similar to the values observed for n-alkanethiolates on Au and Ag substrates.3,4

By contrast, values of the injection current J0(V = +0.5 V)—the limiting value of current for an ideal junction with no hydrocarbon present (d = 0), but with all the interfaces and characteristics of junctions containing the SAMs—vary from ∼10−3 A cm−2, estimated from single-molecules approaches3,10 and measured for graphene11 and evaporated gold12 top-electrodes, to ∼10−2 A cm−2, observed in large-area junctions using, as top-electrodes, conductive polymers,13 Hg-drops supporting an insulating organic film (Hg-SAM),14−16 and Ga2O3/EGaIn tips.17−23 Why is there high consistency in values of β, but broad inconsistency in values of J0(V) within these systems?

A priori, at least four factors might contribute to differences in J0(V) among methods of measurements:

(i) In large-area junctions, assuming that the effective electrical contact area (Aelec) —the area through which current actually passes—coincides with the geometrical contact area (Ageo) estimated by optical microscopy could result in errors in the conversions of values of current into current densities. Contact between surfaces occurs only through asperities distributed on the surfaces, which are always rough to some extent; in addition, only a fraction of the true, physical contact area is conductive.21−24 Estimations of the effective contact area from measurements of adhesion and friction between surfaces indicate that values of Aelec/Ageo vary in the range 10−2−10−4, depending on the hardness of the materials, the heights, widths, and number of asperities on both surfaces, and loads applied to the contacts.22,23,25−27

Received: August 20, 2013
Published: November 4, 2013
(ii) The resistivities of the SAM/electrode contacts might vary due to the nature of the interactions at the top-interface (e.g., covalent bonding versus van der Waals contacts), to differences in the resistivities of the electrode materials, and to the presence of adsorbed insulating impurities.

(iii) The preparation of the top-electrode might damage the SAM (e.g., by reaction of hot metal atoms condensing on top of the SAM, by formation of metal filaments that partially or completely bridge the SAMs, and/or by displacing the SAM).

(iv) The range may also, to some extent, be an artifact: values of \( J_0 \) have often been determined by long extrapolations from small ranges of lengths and based on data characterized by large (and often not statistically determined) dispersions in measured values of current densities for individual \( n \)-alkanethiollate.

There has been much speculation about the relative importance of these factors, but there is little experimental evidence with which to decide among them. Review articles31,32 have considered (approximately) that the electrical behavior of different types of junctions might be influenced by the bulk resistivities of the materials used for the top-electrodes. We observe, however, that correlation of the structures of the molecules making up the SAM with rates of charge transport through these molecules would be impossible if the electrical properties of the top-electrode were to dominate the behavior of the junctions. By contrast, the consensus on the value of \( \beta \) for tunneling across SAMs of \( n \)-alkanethiolates (\( \beta = 0.73 - 0.89 \) Å\(^{-1} \); \( \beta = 0.9 - 1.1 \) nC\(^{-1} \)) strongly suggests that these junctions capture details that are characteristic of charge transport through molecules.

We17,19,20,33 and others38–40 have been developing \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) soft top-electrodes to contact SAMs formed on template-stripped Au and Ag substrates. We have previously reported41 that the layer (average thickness of \( \sim 0.7 \) nm in simple, mechanically unnested systems) that spontaneously forms on the surface of \( \text{EGaIn} \) electrodes consists primarily of \( \text{Ga}_2\text{O}_3 \), and that this \( \text{Ga}_2\text{O}_3 \) layer is redox-inactive in the range \( V = \pm 1 \) V.44 Two of the remaining areas that still need better definition are the effective area of electrical contact between the SAM and the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) top-electrode, and the resistance of the \( \text{Ga}_2\text{O}_3 \).

This paper reaches five major conclusions:

(i) In junctions using conical \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) electrodes on top of SAMs formed on template-stripped silver substrates, the effective electrical contact area is \( \sim 10^{-3} \) the geometrical contact area (measured by optical microscopy).

(ii) The resistance of the \( \text{Ga}_2\text{O}_3 \) layer is lower than the resistance of the SAM of the shortest \( n \)-alkanethiolate (\( \text{Ag}^{25-}\text{SAM} \)) and makes no significant contribution to the resistance of the junction for any length of \( n \)-alkanethiolate group (Figure 1).

(iii) Flattening and stabilizing the surface of the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) tip reduces (by \( \sim 60\% \)) the dispersion in values of \( \log(J/V) \).

(iv) For junctions having the structure \( \text{Ag}^{25-}\text{SR}/\text{Ga}_2\text{O}_3/\text{EGaIn} \) (\( \text{Ag}^{25} = \text{template-stripped silver substrate}; \ R = \text{C}_n\text{H}_{2n+1} \), with \( n = 0 - 18 \)), \( J_0 = 10^{3.6\pm0.1} \) A cm\(^{-2} \) at \( V = +0.5 \) V. This value of \( J_0 \) is much more accurate than previous estimates, in part because we can measure tunneling currents through short-chain \( (n = 1 - 4) \) alkyl groups.

(v) Approximating the effective electrical contact area by the geometrical contact area leads to a significant overestimation of the electrical contact area and to an underestimation of the effective value of \( J_0 \). Correcting the value of \( J_0 \) determined experimentally by the estimated ratio \( A_{\text{eff}}/A_{\text{geo}} = 10^{-4.02\pm0.5} \) gives \( J_0 = 10^{3.9\pm0.8} \) A cm\(^{-2} \) (\( V = +0.5 \) V); this correction reconciles the value of \( J_0 \) for \( \text{Ag}^{25}\text{-SAM/}\text{Ga}_2\text{O}_3/\text{EGaIn} \) junctions with the values of \( J_0 \) reported for single-molecule approaches,5–9 graphene,11 and evaporated gold12 electrodes (\( 10^{8} - 10^{9} \) A cm\(^{-2} \)).

We emphasize that the correction of the electrical contact area has no influence on appropriately designed physical-organic studies, since these studies rely entirely on comparisons of tunneling currents across different organic groups for which the \( \text{Ag}^{25}\text{-SR} \) and the SAM/\( \text{Ga}_2\text{O}_3 \) interfaces will have the same properties. Top-interfaces involving SAMs formed with different types of molecules, and with different electronic structures (e.g., \( \text{Ag}^{25}\text{-alkyl} \) and \( \text{Ag}^{25}\text{-S-aromatic} \), may be different for various reasons. In this work, we thus assume that correction of the values of current density \( J(V) \) for the effective electrical contact area is unnecessary for physical-organic studies comparing SAMs derived from HSC\(_n\). For this type of studies, our estimation of \( J_0 \) is a value that is particularly accurate because it does not involve the long extrapolation from \( n = 10 - 18 \) to \( n = 0 \) characteristic of most prior work—provides a reference value that can be used to test the quality of data for tunneling across \( n \)-alkanethiolates collected in different laboratories using conical \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) tips.

**BACKGROUND**

\( \text{Ga}_2\text{O}_3/\text{EGaIn} \) as a Material for Top-Electrodes. We are developing liquid top-electrodes of eutectic gallium indium alloy (EGaIn) for studies of charge transport through SAMs. Upon exposure to air, EGaIn forms (essentially instantaneously...
Figure 2. (A) Structure of AgTS-SAM//Ga2O3/EGaIn junctions. (B) Components of the resistance of the junction (Rj): RSAM tunneling resistance across the SAM; RGa2O3, resistance of the Ga2O3 layer; lAg–S, length of the bottom AgTS–S covalent contact; lvdW, thickness of the top SAM//Ga2O3 van der Waals interface; d, length of the tunnel barrier established by the alkyl chain. Assuming a through-bond mechanism, d coincides with the length of the alkyl chain. J0 is defined as the current across a junction with d = 0.

The tunneling resistance RSAM originates, in principle, from three components (Figure 2): (i) the resistance of the van der Waals top-interface, which has thickness lvdW; (ii) the resistance of the tunneling barrier established by the alkyl chain (for a through-molecule transport, the length d of this tunnel barrier is given by the length of the alkyl chain); and (iii) the resistance of the Ag–S covalent contact, whose length is lAg–S. Adopting, for these three components, the formalism of the Simmons model, the resistance of the tunnel gap can be (formally) written as

\[ R_{SAM} = R_0^c e^{-\beta_{vdW} lvdW} e^{-\beta_{Ag–S} lAg–S} e^{-\beta d} \]  

(3)

In eq 3, R0 accounts for the electronic properties of the surfaces of the AgTS substrate and of the Ga2O3 layer; \( \beta_{vdW} \) and \( \beta_{Ag–S} \) are the hypothetical decay factors for tunneling across the Ag–S and the SAM//Ga2O3 van der Waals interface, respectively; and \( \beta \) is the tunneling decay factor characteristic of n-alkanes.

If RGa2O3, R SAM, the electrical behavior of the junction is dominated by tunneling across the SAM (Rj ~ R SAM), and trends in J(V) with the structure of the molecules in the SAM will be useful in understanding the relationship between molecular structures and tunneling rates. If, however, the resistance of the Ga2O3 were similar to (RGa2O3, R SAM) or larger than (RGa2O3 > R SAM) that of the SAM, interpretation of data for charge transport through SAMs could be difficult or impossible.

In a previous study, our group estimated a value of the specific resistance (i.e., the resistance per unit area) of the Ga2O3 layer as RGa2O3 = 4 × 10^-2 Ω cm^2. This value of RGa2O3 was ~10^3 times lower than that of a SAM composed of SC9, the shortest molecule studied at that time. We thus concluded that, for medium-length SAMs (n = 9~18), the values of J(V) were determined by the SAM; this inference did not automatically apply to short-chain SAMs (which were not examined in previous studies). In this work, we correct this...
Table 1. Comparison of Values of Injection Tunnel Current $J_\theta(V = +0.5 \text{ V})$ and Tunnel Decay Factor $\beta$ for n-Alkanethiolates (SC$_n$) Reported (or Estimated) for Different Types of Junctions

<table>
<thead>
<tr>
<th>type of junction</th>
<th>top-electrode</th>
<th>bottom-electrode</th>
<th>values of $n$</th>
<th>log$<em>{10} (J</em>\theta/A \text{cm}^{-2})$</th>
<th>$\beta$ (nC$^{-1}$)</th>
<th>ref</th>
</tr>
</thead>
<tbody>
<tr>
<td>Au-SAM/Ag</td>
<td>conductive polymer</td>
<td>as-dep$^a$</td>
<td>8, 10, 12, 14, 16</td>
<td>$\sim 2$</td>
<td>1.10 ± 0.04</td>
<td>13</td>
</tr>
<tr>
<td>Ag SAM//Ga$_2$O$_3$/EGaIn</td>
<td>Ga$_2$O$_3$/EGaIn (cone)</td>
<td>TS</td>
<td>9, 11, 13, 15, 17</td>
<td>1.9</td>
<td>1.00 ± 0.02</td>
<td>18</td>
</tr>
<tr>
<td>Ag SAM//Ga$_2$O$_3$/EGaIn</td>
<td>Ga$_2$O$_3$/EGaIn (cross-bar)</td>
<td>TS</td>
<td>12, 14, 16, 18</td>
<td>$\sim 2.5$</td>
<td>0.95 ± 0.2</td>
<td>20</td>
</tr>
<tr>
<td>Ag SAM//Ga$_2$O$_3$/EGaIn</td>
<td>Ga$_2$O$_3$/EGaIn (cone)</td>
<td>TS</td>
<td>10, 12, 14, 16, 18</td>
<td>2.5</td>
<td>0.97 ± 0.02</td>
<td>18</td>
</tr>
<tr>
<td>Ag SAM//Ga$_2$O$_3$/EGaIn</td>
<td>Ga$_2$O$_3$/EGaIn (cone)</td>
<td>TS</td>
<td>10, 12, 14, 16</td>
<td>$\sim 3$</td>
<td>1.1 ± 0.2</td>
<td>19</td>
</tr>
<tr>
<td>Ag SAM//Ga$_2$O$_3$/EGaIn</td>
<td>Ga$_2$O$_3$/EGaIn (cone)</td>
<td>TS</td>
<td>0−18</td>
<td>$3.6 \pm 0.3$</td>
<td>0.92 ± 0.02</td>
<td>this</td>
</tr>
<tr>
<td>Ag SAM//SAM-Hg$^b$</td>
<td>Hg-SC$_{16}$</td>
<td>as-dep</td>
<td>8, 10, 12, 14, 16</td>
<td>$\sim 3$</td>
<td>1.0</td>
<td>15</td>
</tr>
<tr>
<td>Au-SAM-Au</td>
<td>Au nanoskiving</td>
<td>nanoskiving</td>
<td>12, 14, 16</td>
<td>3.2</td>
<td>0.94</td>
<td>51</td>
</tr>
<tr>
<td>Au-SAM//PEDOT/Au</td>
<td>PEDOT:PSS</td>
<td>as-dep</td>
<td>8, 10, 12, 14</td>
<td>$\sim 5$</td>
<td>0.76</td>
<td>47</td>
</tr>
<tr>
<td>Hg SAM//SAM-Hg$^c$</td>
<td>Hg</td>
<td>liquid metal</td>
<td>18, 20, 22, 24, 28</td>
<td>$\sim 6$</td>
<td>0.9</td>
<td>50</td>
</tr>
<tr>
<td>Hg SAM//Hg$^d$</td>
<td>Hg</td>
<td>liquid metal</td>
<td>9−12, 15, 16, 18</td>
<td>$\sim 6$</td>
<td>1.04 ± 0.07</td>
<td>49</td>
</tr>
<tr>
<td>nSi-SAM//Hg</td>
<td>n-Si$^d$</td>
<td>14, 16, 18</td>
<td>6.5$^b$</td>
<td>0.9 ± 0.2</td>
<td>3, 4</td>
<td></td>
</tr>
<tr>
<td>Au-SAM//graphene</td>
<td>graphene</td>
<td>TS</td>
<td>8, 12, 16</td>
<td>8.3</td>
<td>1.02 ± 0.1</td>
<td>11</td>
</tr>
<tr>
<td>Au-SAM-Au</td>
<td>Au evaporated</td>
<td>TS</td>
<td>8, 12, 16</td>
<td>$\sim 8$</td>
<td>0.98 ± 0.03</td>
<td>12</td>
</tr>
<tr>
<td>Au-SAM-Au</td>
<td>STM tip</td>
<td>single crystal$^f$</td>
<td>6, 8, 10</td>
<td>8.9</td>
<td>1.09</td>
<td>5−7</td>
</tr>
<tr>
<td>Au-SAM-Au</td>
<td>AFM tip</td>
<td>single crystal</td>
<td>6, 8, 10, 12</td>
<td>8.2</td>
<td>0.8</td>
<td>8, 9</td>
</tr>
</tbody>
</table>

$^a$Conductive polymer = polyphenylenevinylene-type polymer. $^b$$J_\theta$ extrapolated at the length of the top-SAM. Including the top-SAM in the tunnel barrier of the junction yields log$_{10} (J_\theta) = 6$. $^c$$J_\theta$ not reported by the authors of the original paper; we estimated $J_\theta$ from published data. $^d$Junction held under electrochemical control. $^e$as-dep = as-deposited, rough metal substrate. $^f$Templated material, flat metal substrate. $^g$N-doped silicon. $^h$J$_\theta$ calculated from contact conductance of a single molecule reported in the original article. $^i$Flat terraces of single-crystal surfaces. $^j$Value to $R_{Ga_2O_3} = 3.3 \times 10^{-4}$ Ω-cm$^2$; this change does not alter our understanding of the junction.

Properties of the SAM//Ga$_2$O$_3$/EGaIn Top-Contact, and Sources of Uncertainty. The Ga$_2$O$_3$/EGaIn top-electrode is in van der Waals contact with SAMs of n-alkanethiolates, which terminate in CH$_3$ groups. Because the formation and manipulation of conical tips generate a Ga$_2$O$_3$ layer that is variable in thickness, and that further buckles and unfolds during manipulation, the surface of the top-electrode is rough. The surface of the Ag$^{35}$ substrate, and thus the topography of the top-surface of the SAM, is also rough (due to Steps, grain boundaries, and other defects in the silver surface, the topography of the top-surface of the SAM, is also rough (due to steps, grain boundaries, and other defects in the silver surface, and to irregularities in the order and structure of the SAM$^{37}$). This heterogeneity in structure, topography, and thickness results in an effective electrical contact area that is smaller than the area of the geometrical contact estimated by microscopy.

In addition to the heterogeneities in the Ga$_2$O$_3$ film, other factors that can contribute to uncertainties in data collected with Ga$_2$O$_3$/EGaIn top-electrodes include (i) the presence of adventitious contaminants adsorbed on the tip and/or the SAM (although a methyl-terminated surface has a low interfacial free energy and a low tendency to adsorb impurities, metals and metal oxides have high surface energies) and (ii) the formation of conductive filaments between the top-electrode and the metal substrate.$^{38−30}$

Charge Transport across SAMs. The Simmons model$^{1,2}$ provides an approximate analytical equation (eq 1) for charge tunneling through a potential barrier established by an organic insulator; in this model, the value of the decay factor $\beta$ is determined by the height of the potential barrier. Currently, no molecular theory correlates experimental values of $J(V)$ and $\beta$ with molecular structure, and the Simmons model may be inappropriate and incomplete$^{47,48}$ (especially for organic SAMs more complicated than simple n-alkanes, or when these SAMs involve electronically conductive regions, although we observed that charge transport across a variety of complex structures is very similar to tunneling through n-alkanethiolates$^{37}$). Nonetheless, in the absence of a more developed theory, the simplified Simmons equation has been adopted as the theoretical standard for analyses in studies of charge tunneling across organic molecules because, in the low-bias regime, it reduces the tunneling problem to the determination of just two parameters: $\beta$ and $J_\theta$.

Values of $J_\theta$ for tunneling across n-alkanethiolates estimated by different techniques differ by more than 10$^7$ A·cm$^{-2}$; these techniques use a variety of different top-electrodes, which include Hg-drops, Hg-SC$_n$H$_{14−16,50}$ (that is, Hg-drops supporting a monolayer of S(CH$_2$)$_n$CH$_3$ with $n = 11, 13, 15$), conductive polymers, Ga$_2$O$_3$/EGaIn$^{18−20}$, tips, evaporated Au electrodes, Au electrodes fabricated via nanoskiving, graphene, and scanning tunneling microscopy (STM)$^{5−7}$ and atomic force microscopy (AFM)$^{50}$ tips. Table 1 summarizes values of $J_\theta(V = +0.5 \text{ V})$ reported or estimated for these junctions.

Experiments with different junctions using the same material for the top-electrode have given substantial differences in $J_\theta$; this variability is in contradiction with theory and intuition, both of which would predict that the same materials would give the same values of $J_\theta(V)$. Our hypothesis is that differences in $J_\theta$ arise from differences in the procedures used to fabricate the top-electrode, rather than from differences in materials. Junctions using Au electrodes directly evaporated$^{12}$ on top of the SAM yielded a value of $J_\theta$ ($10^4$ A·cm$^{-2}$) that was 10$^4$ that reported for junctions using Au top-electrodes fabricated via nanoskiving$^{51}$ ($J_\theta = 10^{12}$ A·cm$^{-2}$). We believe both values are correct, but specific to different experiments. The different behavior probably reflects differences in the values of $A_{\text{geo}}/A_{\text{sub}}$ due to differences in the roughness of the electrodes.

Using highly conductive polyphenylenevinylene layers$^{13}$ and Hg-drops carrying an organic insulator$^{15}$ as top-contacts on SAMs formed on rough (as-evaporated) substrates yielded values of $J_\theta$ ($10^5−10^6$ A·cm$^{-2}$) close to the values of $J_\theta$ obtained using highly conductive, but rough, Ga$_2$O$_3$/EGaIn conical tips.$^{16,20}$ By contrast, values of $J_\theta$ ($10^9$ A·cm$^{-2}$) are reported for large-area junctions using flat metal substrates and flat (e.g., evaporated Au$^{12}$) top-electrode.
For junctions using Hg-drops on top of alkyl chains anchored to heavily doped Si surfaces, Cahen and co-workers reported a value of \( J_0 = 10^{6.5} \text{ A cm}^{-2} \) for p-Si substrates, and a value of \( J_0 = 10^{4} \text{ A cm}^{-2} \) for n-Si substrates\(^{18}\). For the system with \( J_0 = 10^{4} \text{ A cm}^{-2} \), fitting the Simmons equation to experimental \( J-V \) curves for individual \( n \)-alkanes required a correction of the contact area by a factor of \( \sim 10^{-4} \) in order to get meaningful fitting parameters\(^{3} \) (30 m\(^2\) contact area required by the fitting, over a geometrical contact area of \( 5 \times 10^4 \text{ m}^2 \)). Cahen et al. argued that theoretical modeling of experimental tunneling rates characterized by \( J_0 = 10^{4} \text{ A cm}^{-2} \) "may lack physical relevance."\(^{3} \)

These results indicate that different properties (we believe primarily topographies of the surfaces) for top- and bottom-electrodes—and not the resistances of the corresponding bulk materials—determine the spread of the experimental values of \( J_0 \) across different methods (Table 1).

## EXPERIMENTAL DESIGN

**SAMs of \( n \)-Alkanethiols with Even Numbers of Carbon Atoms.** \( n \)-Alkanethiols (\( \text{CH}_n\text{CH}_2\text{SH} \)), represented here as \( \text{SC}_n \), are commercially available in a range of lengths; they are accepted as the simplest model system for physical-organic studies of tunneling through SAMs. We note that the complexity of structural features of SAMs of \( n \)-alkyl chains—e.g., packing density, insoluble multilayer metal thiolate "soaps" for silver, defects, roughness of the underlying metal—makes these SAMs more complex than they first seem.\(^{29} \)

We collected \( J-V \) data for SAMs composed of \( \text{SC}_n \), with even numbers of carbons from \( n = 2 \) to \( n = 18 \). We excluded long (\( n > 5 \)) \( n \)-alkanethiols with odd numbers of carbons because they behave differently from those with even \( n \), and require a separate analysis.\(^{48,19} \)

**Measurements on Short \( n \)-Alkanethiols with Odd Numbers of Carbon Atoms.** In order to study the frequency of the failure of the junctions, and to provide values of \( f(V) \) for SAMs composed of short molecules, we measured rates of charge transport through SAMs formed from \( \text{CH}_3\text{SH} \) (\( \text{SC}_1 \)), and \( \text{CH}_3\text{(CH}_2\text{)}_2\text{SH} \) (\( \text{SC}_3 \)), and through AgTS-SH (\( \text{SC}_0 \)). (We formed \( \text{CH}_3\text{SH} \) and \( \text{H}_2\text{Sb} \) by extruding a \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) drop)\(^{18,49} \)

**Template-Stripped Substrates.** We formed SAMs on template-stripped Ag (\( \text{Ag}^{5+} \)) substrates.\(^{46,49} \) Template-stripping provides surfaces characterized by large flat terraces (average area of terraces \( \sim 0.13 \text{ m}^2 \)). Template-stripped surfaces give larger effective electrical contact areas than "as-evaporated" top-surfaces;\(^{56} \) the value of \( A_{\text{eff}}/ A_{\text{geo}} \), however, limited by the roughness of the terraces, by the size of the silver grains, and by the width and the depth of grooves between grains. Forming SAMs on silver template-stripped substrates yielded \( \sim 90\% \) of nonshorting junctions.

**Fabrication of Flattened Conical Tips, and Tips on Top of the SAM.** The apparent non-Newtonian properties of the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \)\(^{53} \) enable several procedures for the fabrication of the top-electrode. For this paper, we used what we call "flattened" conical tips. Although these tips are characterized by an effective electrical contact area that we know to be less than the nominal contact area we measure by optical microscopy, they can be quickly and easily fabricated and used in physical-organic studies, where convenience and the ability to generate large number of data are more important in correlating different molecular systems with values of \( f(V) \) than is high precision (this type of use assumes, of course, that \( J_0/V \) is the same across all the junctions formed with different tips). Figure 3 summarizes the five steps of the procedure we used to fabricate flattened conical tips: (1) We extruded a \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) drop from a 10-\text{ L} syringe. (In order to keep the weight of the EGaIn column constant in all junctions, we always used 2 \text{ L} of EGaIn.) (2) With a micromanipulator, we brought the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) drop in contact with a clean metal substrate (usually Au\(^{55} \)). (3) We slowly (\( \sim 0.5 \text{ mm/s} \)) pulled the syringe away from the surface to form a \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) neck. (4) By further withdrawing the syringe, we broke the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) neck and obtained a top-conical tip. The surface of this as-fabricated conical tip is characterized by asperities and whiskers randomly formed while forming and breaking the neck. Analysis of data collected with these tips revealed that an important source of dispersion in the measured values of \( f(V) \) was the variation of these values from junction to junction, probably due to the progressive deformation of asperities (Supporting Information, Figure S1). (5) We flattened the asperities of the as-fabricated conical tip by touching it three times to a flat, polished \( \text{SiO}_2/\text{Si} \) surface (the type of \( \text{SiO}_2/\text{Si} \) substrates used for template-stripped metal surfaces). We observed that this procedure stiffened the tip and led to more stable contacts. We also observed that running three cyclic voltage scans between \( \pm 2 \text{ V} \) while the tip is in contact with the Si chip further reduced the dispersion in data for \( f(V) \).

We used the flattened conical tips as top-electrodes on Ag\(^{55} \)-SAM substrates (Figure 3, step 6). To form stable contacts, we brought the tips closer to the substrates until we could clearly observe (by optical microscopy) the tip apex wrinkling, or deforming; from this point, current densities did not change for applied forces varying in the range \( 2\sim4 \text{ g cm}^{-2} \). (We thus used the "wrinkling" of the \( \text{Ga}_2\text{O}_3 \) skin on the sides of the conical tip as an indication of the load applied.) We did not explore larger deformation of the tips.

This procedure for the fabrication of flattened tips, and for the formation of stable contacts on top of the SAMs, generated reproducible values of \( J_0/V \), \( \beta \), and \( \log \) among different users. The
standard deviations of values of log|I| measured with these flattened conical tips were by 60% smaller than those observed for as-fabricated tips; flattening the tip, however, had no effect on (log|I|), the mean values of the distributions (Supporting Information, Figure S1). A video of the fabrication of a flattened conical tip is available as Supporting Information.

**Protocol for Collection of Data.** We have observed that data collected with an unstandardized protocol (that is, forming an arbitrary number of junctions, running arbitrary numbers of scans) can broaden data distributions. We have thus introduced a standard procedure for data acquisition, which we call the “1/3/20” protocol. For each individual tip, we formed three junctions (i.e., contacts) in three different places of the AgTS-SAM; for each junction, we recorded 20 J−V traces for forward bias (V = −0.5 V → V = +0.5 V) and 20 J(V) traces for reverse bias (V = +0.5 V → V = −0.5 V). From empirical comparison of procedures, we speculate that, by limiting the number of junctions per tip, the 1/3/20 protocol may avoid collecting data with EGaIn tips contaminated by adventitious impurities. Collecting the same number of data per tip (120 points in total) ensures that all tips have the same statistical weight. The 20 scans are necessary so that we do not statistically overweight instabilities of the current that often occur during the first scans of a junction.18 Collecting more than five scans per junction, however, produces autocorrelated data,18 but this autocorrelation has no influence on the mean values and dispersions of our data sets, because it arises mainly from redundant data.18

**Definition of the Tunnel Injection Current Density J0(V).** In this paper, we define the injection current J0(V) for AgTS-SCn/Ga2O3/EGaIn junctions as the value of J(V) given by eq 3 for d = 0, that is, the value of J(V) for an ideal junction with no alkyl chain, but with all characteristics and interfaces of junctions containing the SAM:

\[
J_0(V) = V/R_{0}^{\alpha} \exp(-\beta_{\text{inj}}V) \exp(-\beta_{\text{kinj}}V^{1/3}) \]

We adopted this definition of J0(V) for two reasons: (1) The value of J0(V) given by eq 4 can be easily estimated by extrapolating to d = 0 values of log|J(V)| for n-alkanethiolates of different lengths. The extrapolation requires that values of log|J(V)| decay with a constant slope (that is, constant \(\beta\)) along the full range of lengths. We recall that the tunnel barrier also includes the Ag−S and SAM/Ga2O3 van der Waals interfaces. But the \(\beta\) factors of the top- and bottom-interfaces are unknown; assuming that the interfaces have the same \(\beta\) as the alkyl chain might lead to errors in the estimation of the value of \(J_0\) (this error might be significant for SAMs formed using anchoring group longer than Ag−S, for example, C−C−R or O−C−R19).

(2) Defining J0(V) for d = 0 gives a value of injection current that incorporates the rates for charge transport across the top- and bottom-interfaces (eq 4). This value of J0(V) can be used to compare the e fiency of charge injection into thioclates with that into other anchoring groups (provided that for these other anchoring groups d = 0 is defined on the first atom to which the alkyl chain is bound, and that the van der Waals top-interface remains unchanged); alternatively, values of J0(V) for SAMs of n-alkanethiolates having different terminal groups can be used to compare the e fiencies of charge injections into van der Waals top-interfaces having different structures.

We point out that the value of J0 given by eq 4 varies linearly with the applied voltage (that is, constant value of \(R_0\)) only in the range of voltages −0.1 V ≤ V ≤ +0.1 V.20 Assuming, however, that for a fixed voltage the value of \(R_0\) is invariant across SAMs of different n-alkanethiolates, in this paper we estimate the value of J0 for the applied voltage V = +0.5 V (and V = −0.5). At V = +0.5 V, rates of charge tunneling follow (qualitatively) the Simmons equation (eq 1); in addition, values of tunneling current across SAMs of the full set of n-alkanethiolates (SCn with n = 1−18) fall within the operative range of our electrometer (105 mA to 0.1 nA). At voltages > +0.5 V (≤ −0.5 V), resonances of the Fermi levels of the electrodes with molecular or interfacial electronic states lead to nonlinear variation of J0 with V54 and the approximate Simmons equation does not describe charge tunneling adequately. In this paper we do not explore the high-bias regime.

Assuming a through-molecule tunneling, we measure the thickness d of the tunnel barrier established by the n-alkyl chains as the distance in angstroms from the S-terminus of the n-alkanethiolates to the distal hydrogen atom closest to the top-electrode (Figure 2). To compare our results with others reported in the literature, we also estimated d as the number of C atoms (nC) of the alkyl backbone. We observe, however, that the length of the molecules as nC does not take into account the contribution of the length of the distal C−H bond (and thus the effective length of the tunnel barrier) differs for these two classes of n-alkanethiolates (Figure S2). It is also evident that the comparison of the electrical behavior of SAMs of n-alkanethiolates with those of SAMs composed of molecules having different structure (e.g., SAMs of aromatic molecules) requires that d be given in Å.

**Statistical Analysis of Data for Current Density across SAMs.** We estimated J0(A−cm−2) and \(\beta\) (A−1cm−1) by least-squares linear regression analysis of values of (log|I|) versus the width d of the tunnel barrier established by the alkyl chains, which we assume to be in their all-trans configuration; (log|I|) is the Gaussian mean value of data for log|I|, where \(J\) is the current density (measured in A−cm−2) at V = +0.5 V, and defined for the geometrical contact area estimated by optical microscopy) through SAMs.

Because experimental data for log|I| are approximately normally distributed for all SAMs, we extracted mean values ((log|I|)) and standard deviations (\(\sigma_{\text{log}}\)) from Gaussian fits (calculated with standard least-squares fitting18) to histograms of data.

**Estimation of the Specific Resistance of Ga2O3/EGaIn Tips.** We estimated the apparent (that is, not corrected for the high-bias electrical contact area) specific resistance \(R_{\text{Ga2O3}}\) (the resistance per unit area, \(\Omega\cdot\text{cm}^2\)) of the Ga2O3/EGaIn conical tips from the specific resistance of junctions with structure HOPG/Ga2O3/EGaIn (HOPG = highly ordered pyrolytic graphite). Because both HOPG and bulk EGaIn are highly conductive materials (\(< 10^{-6} \Omega\cdot\text{cm}\)), the resistance of these junctions is dominated by the resistance of the Ga2O3 layer. The advantages of using HOPG surfaces in measurements of contact conductance are that (i) they provide ultratrace substrates with sub-nanometer roughness, (ii) they do not oxidize in air, and (iii) they can be easily regenerated before each experiment.

**Estimation of the Effective Electrical Contact Area in AgTS-SAM/Ga2O3/EGaIn Conical Tip Juncions.** We define the ratio of the effective electrical contact area (\(A_{\text{geo}}\)) to the geometrical contact area estimated by optical microscopy (\(A_{\text{opt}}\)) as

\[
A_{\text{geo}} = \frac{A_{\text{opt}}}{\text{tip \ SAM}}
\]

where \(A_{\text{geo}}\) and \(A_{\text{opt}}\) are the fractions of the geometrical surface areas that are available for contact respectively in Ga2O3/EGaIn conical tips and in AgTS-SAM substrates; these fractions are defined as the ratios of the effective electrical contact areas to the geometrical contact areas of conical tips (\(A_{\text{geo}}\)) and AgTS-SAMs (\(A_{\text{opt}}\)) in contact with an ideally flat electrode (that is, an ideal electrode with a surface topography that does not reduce the effective electrical contact area). We estimated \(A_{\text{geo}}\) and \(A_{\text{opt}}\) separately.

**Estimation of the Fraction of the Geometrical Surface Area of Conical Tips Available for Contact (\(A_{\text{geo}}\)).** We estimated \(A_{\text{geo}}\) as the ratio of the current density \(J_{\text{geo}}\) flowing through Ga2O3/EGaIn conical tips, to the current density \(J_{\text{tip}}\) yielded by Hg-drop electrodes, in junctions formed with a standard substrate. We assume that Hg-drop electrodes have smooth, conformal surfaces with an area available for contact close to the geometrical surface area (\(A_{\text{geo}}\)). We used Fe3O4 (Fe3O4 = template-striped iron substrate) as standard substrate because it does not amalgamate with Hg. We grew the Fe3O4...
Figure 4. Histograms showing the distributions of values of log|J| at V = +0.5 V across AgTS-SAM//Ga2O3/EGaIn junctions using flattened conical tips. With "Cn" we indicate SAMs of n-alkanethiolates with n carbon atoms. Solid curves represent Gaussian fits. N is the number of data points. Data were collected using the 1/3/20 protocol; no data were excluded. The heights of the bars of the histograms count the number of points (counts) with values of log|J| within the width (0.13) of the bars. For each distribution, the values of the Gaussian mean, median, and mode (the value of log|J| with the highest bar) differed by <0.1.
layer thermally with a specific resistance ($R_{Ga2O3}$, 10 $\Omega \cdot$ cm$^2$) that is 
$\sim 10^4$ higher than the apparent specific resistance of the Ga$_2$O$_3$ layer estimated using HOPG ($R_{Ga2O3}$ = 3.3 $\times$ 10$^{-4}$ $\Omega$-cm$^2$). Because $R_{Ga2O3}$, $R_{Ga2O3}$ by experimental design, the specific resistances of both Ga$_2$O$_3$/EGaIn and Hg-drop-based junctions are determined by $R_{Ga2O3}$, and, at a given voltage $V$, they must give the same effective current densities:

$$I_{tip} = \frac{V}{R_{Ga2O3}} = I_{Hg}$$

(6)

In eq 6, $I_{tip}$ is the current flowing through the effective electrical contact area $A_{tip}$ in junctions using Ga$_2$O$_3$/EGaIn conical tips, and $I_{Hg}$ is the current through the effective electrical contact area $A_{Hg}$ in junctions using Hg-drops.

We define the effective electrical contact area for Fe$_{TS}$/Fe$_{O2}$//Ga$_2$O$_3$/EGaIn junctions as $A_{geo,tip} = A_{geo,Hg}$, where $A_{geo,tip}$ is the geometrical contact area of Ga$_2$O$_3$/EGaIn conical tips on the Fe$_2$O$_3$ substrate. Analogously, we define the effective electrical contact area of Fe$_{TS}$/Fe$_{O2}$//Hg junctions as $A_{geo,Hg}$ = $A_{geo,Hg}$, Fe$_{TS}$/Fe$_{O2}$ with $A_{geo,Hg}$ being the geometrical contact area of Hg-drops on the Fe$_2$O$_3$ substrate. The fraction $F_{Fe2O3}$ quantifies the contribution of the roughness of the Fe$_2$O$_3$ layer to the effective contact area. Equation 6 thus becomes

$$I_{tip} = \frac{V}{R_{Ga2O3}} = I_{Hg}$$

(7)

The fraction $F_{Ga2O3}$ was the same for both junctions because we used the same Fe$_{TS}$/Fe$_{O2}$ chip for all measurements. We thus obtain

$$I_{tip} = \frac{V}{R_{Ga2O3}} = I_{Hg}$$

(8)

Experimenteral current densities, however, are calculated for the geometrical contact areas, that is,

$$I_{geo,tip} = \frac{I_{tip}}{A_{geo,tip}}$$

and

$$I_{geo,Hg} = \frac{I_{Hg}}{A_{geo,Hg}}$$

(9)

Here, $I_{geo,tip}$ is the experimental current density for junctions formed with Ga$_2$O$_3$/EGaIn tips, and $I_{geo,Hg}$ is the experimental current density for junctions formed with Hg-drop junctions. By substituting eq 9 into eq 8, we obtain

$$I_{tip} = \frac{I_{geo,tip}}{I_{geo,Hg}}$$

(10)

We estimated $I_{geo,tip}$ and $I_{geo,Hg}$ as mean values $\langle I_{geo,tip} \rangle$ and $\langle I_{geo,Hg} \rangle$ of data for current density at $V = +0.5$ V — collected following the 1/3/20 protocol—for Fe$_{TS}$/Fe$_{O2}$//Ga$_2$O$_3$/EGaIn conical tips, and for Fe$_{TS}$/Fe$_{O2}$//Hg-drop junctions.

**Estimation of the Fraction of the Geometrical Surface of Ag$_{TS}$-SAM Substrates Available for Contact ($\alpha_{SAM}$).** We estimated $\alpha_{SAM}$ from digital analysis of a STM image of a Ag$_{TS}$-SAM substrate using

$$\alpha_{SAM} = \frac{q}{Q}$$

(11)

where $q$ is the number of pixels within 2 $\AA$ from the top-most average plane of the digital image, and $Q$ is the total number of pixels. The length used (2 $\AA$) represents the variation of the length of the tunnel gap (±1 $\AA$, that is, $\sim \pm 0.5$) calculated from the average standard deviation of $\log(J)$ ($\sigma_{log} = 0.3$) considering $\beta = 0.75$ $\AA^{-1}$ for n-alkanethiols. We used a 900 nm $\times$ 900 nm STM image of a Ag$_{TS}$-SC$_{18}$ substrate that did not present valleys or asperities that would require, for the estimation of $\alpha_{SAM}$ that we take into account the partial adaption of the Ga$_2$O$_3$/EGaIn tip to the topography of the surface.

### RESULTS AND DISCUSSION

The yield of working junction is independent of the length of the molecule. We observed an average yield of working junction of $\sim 90\%$ for all chain lengths (including $n = 0$). For the first time, we have been able to measure charge transport through SAMs composed of short molecules of SC$_n$ ($n = 0$–6); the yields of working junctions for these short SAMs were approximately the same as those for the longer ones ($n = 8$ to $n = 18$). Yields of working junctions for individual n-alkanethiols are summarized in Table S1.

The high yield observed for the very thin SAMs ($n = 1$–4) implies that junctions using Ga$_2$O$_3$/EGaIn junctions can sustain electric fields as high as 1 GV m$^{-1}$. In a previous work, we reported that junctions formed with Hg-drops broke down at electric fields $\sim 0.8$ GV m$^{-1}$. These results suggest that the breakdown electric field might be influenced by the mechanical properties (e.g., stiffness, rigidity) of the top-electrode, or by the resistance to lateral spreading under electrostatic pressure of the SAM on Ag$_{TS}$ (as opposed to Hg$^{66}$). Junctions using solid, conductive AFM tips as top-electrodes can sustain electric fields as high as 3 GV m$^{-1}$; as such, they are used in studies of charge transport at applied voltages $> 2$ V.$^{57}$

**Statistical Analysis of Data for log|$J$|**. Figure 4 summarizes histograms of data for log|$J$| (at $V = +0.5$ V) for SAMs of n-alkanethiols from SC$_0$ to SC$_{18}$ formed on Ag$_{TS}$.

These histograms approximately fitted Gaussian curves, from which we extracted the mean values (log|$J$|) and standard deviations $\sigma_{log}$. For all molecules, Gaussian mean, median, and mode (the value of log|$J$| with the highest frequency) differed by $<0.1$. Statistical analysis of histograms for log|$J$| at $V = +0.5$ V (summarized in Figure S3) led to mean values (log|$J$|) and standard deviation $\sigma_{log}$ similar to those obtained for $V = +0.5$ V, revealing a symmetry of tunneling rates in the range of voltages $V = \pm 0.5$ V. The Gaussian fits yielded values of $\log |J| = 0.3$ (which corresponds to values of $J(V)$ from 0.5$\times$X$\langle J(V) \rangle$ to 2$\times$X$\langle J(V) \rangle$) for SAMs of long molecules (SC$_6$–SC$_{18}$), and an average value of $\log |J| = 0.7$ (that is, values of $J(V)$ between 0.2$\times$X$\langle J(V) \rangle$ and 5$\times$X$\langle J(V) \rangle$) for SAMs of the short n-alkanethiols (SC$_1$–SC$_4$). The difference in the value of $\log |J|$ between short and long molecules might be caused by a different structure of the SAM. SAMs of n-alkanethiols with $n < 5$ are believed to have disordered, liquid-like structure, whereas long molecules form compact, crystalline films.$^{32}$

**Calculating $J_0$ and $\beta$**. Figure 1 shows that values of (log|$J$|) (at both $V = +0.5$ and $-0.5$ V) decreased linearly with the length $d$ of the S-(CH$_2$)$_n$-1 group ($d$ is given also as the number of carbon atoms nC on the top-axis of the plot). This plot is compatible with the simplified Simmons equation for tunneling (eq 1). For $V = +0.5$ V, the linear regression analysis yielded (log|$J_0$) = 3.6 $\pm$ 0.3 ([J$_0$] = A cm$^{-2}$); this value was statistically indistinguishable from that obtained for $V = -0.5$ V (log|$J_0$) = 3.4 $\pm$ 0.3, [J$_0$] = A cm$^{-2}$). These values of $J_0$ estimate the current density injected across the Ag$_{TS}$–S and the Ga$_2$O$_3$/SAM interfaces into the alkyl chain. For both $V = +0.5$ and $-0.5$ V, the slope of the linear regression analysis gave a value of the tunnel decay factor of $\beta = 0.75 \pm 0.02$ Å$^{-1}$ ($\beta = 0.92 \pm 0.02$ nm$^{-1}$).

The linear decay of the values of log|$J$| across the full range of lengths suggests that the details of the structure of the SAM—especially liquid-like or crystalline—do not influence charge tunneling across these SAMs. Short n-alkanethiols ($n < 5$) form SAMs with disordered, liquid-like structures, while long n-
alkanethiolates form compact SAMs with crystalline structure. The fact that the same value of $\beta$ applies across different lengths of $n$-alkyl groups, and across different experimental technologies, provides further evidence of a substantial insensitivity of charge transport to the details of the structure of the SAM. In this conclusion, we disagree with recent work by Vilan et al. \(^{58}\)

**Ohmic Electrical Transport through the Ga$_2$O$_3$ Layer.**

The HOPG//Ga$_2$O$_3$/EGaIn junction yielded 100% of working junctions. For this junction, $J$ varied linearly with the voltage (Figure 5) and confirmed the ohmic transport across the Ga$_2$O$_3$ layer previously reported. \(^{34}\) Linear regression of the $J-V$ average trace yielded an ohmic conductance (slope) of $\sim 3.0 \times 10^3 \text{ A cm}^{-2} \cdot \text{V}^{-1}$, from which we estimated an apparent specific resistance (i.e., the resistance per unit area, and not corrected for the effective electrical contact area) of the Ga$_2$O$_3$ layer of $R_{Ga2O3} = 3.3 \times 10^{-4} \Omega \cdot \text{cm}^2$. The measured specific resistance of the Ga$_2$O$_3$ layer was lower—by a factor of $\sim 10$—than the specific resistance of the SAM of the shortest alkanethiolate SC$_1$ ($R_{SC1} = 1 \times 10^{-3} \Omega \cdot \text{cm}^2$).

In our previous work, \(^{34}\) we used copper wires with a diameter of 80 $\mu$m to estimate a resistance of the Ga$_2$O$_3$ layer of $R_{Ga2O3} = 4 \times 10^{-2} \Omega \cdot \text{cm}^2$. We believe that this estimation was less accurate than the one we report here for two reasons: (i) due to the shape and size of the wires, we were not able to measure accurately the geometrical contact area of the Cu wires on Ga$_2$O$_3$/EGaIn droplets, and (ii) we did not take into account the contribution to the resistance of the Cu/CuO$_x$/Ga$_2$O$_3$/EGaIn contact of the native oxide CuO$_x$ passivating the surface of the Cu wires. These Cu/CuO$_x$/Ga$_2$O$_3$/EGaIn contacts, however, exhibited ohmic transport.

**The effective electrical contact area of Ag$^{TS}$-SAM//Ga$_2$O$_3$/EGaIn junctions using flattened conical tips was $\sim 10^{-4}$ the geometrical contact area.** To estimate the effective electrical contact area, we calculated the fraction of the surface area available for contact for Ga$_2$O$_3$/EGaIn conical tips ($\alpha_{\text{tip}}$), and for Ag$^{TS}$-SAM substrates ($\alpha_{\text{SAM}}$).

**Estimation of $\alpha_{\text{tip}}.$** Figure 6 shows the histograms for data for log|$J$ and the relative Gaussian fits for junctions having structures Fe$^{TS}$/Fe$_2$O$_3$/Hg-drops and Fe$^{TS}$/Fe$_2$O$_3$/Ga$_2$O$_3$/EGaIn (flattened conical tips). The resistance of the junction formed with Hg-drops was determined by the specific resistance of the Fe$_2$O$_3$ layer. Because, by experimental design, the specific resistance of this Fe$_2$O$_3$ layer was $\sim 10^4$ the specific resistance of the Ga$_2$O$_3$ layer (estimated from measurements of contact resistance of Ga$_2$O$_3$/EGaIn tips on HOPG), also the specific resistance of the Ga$_2$O$_3$/EGaIn-based junctions was determined by the resistance of the Fe$_2$O$_3$ layer. Having approximately the same specific resistance ($\sim R_{Fe2O3}$) at a fixed voltage, both Ga$_2$O$_3$/EGaIn conical tips and Hg-drops should have given the same value of current density. The mean value (at $V = +0.5 \text{ V}$, $\langle\log|J|\rangle = -4.2 \pm 0.4$) of the current density measured with Ga$_2$O$_3$/EGaIn conical tips, however, was $\sim 10^{-3}$ the mean current density measured with the Hg-drop (at $V = +0.5 \text{ V}$).
+0.5 V, \langle \log |I_{d}| \rangle = -1.3 \pm 0.1). Using these experimental values of current densities, from eq 10 we estimated \( J_{\text{tip}} = 10^{-3} \Omega^{-0.5} \). We emphasize that, by experimental design, the difference in \( I(V) \) between \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) and \( \text{Hg}-\text{drop-based} \) junctions cannot be explained by the difference between the resistances of \( \text{Hg} \) and of the \( \text{Ga}_2\text{O}_3 \) layer.

Estimation of \( \alpha_{\text{SAM}} \). Figure 7A shows a STM image of a SAM of \( \text{SC}_{10} \) on \( \text{Ag}^{18} \). By digital analysis of the pixels (eq 11), we estimated that \( \sim 12\% \) of the geometrical surface area of the \( \text{Ag}^{18} \)-SAM substrate was available for contact (Figure 7B), that \( \alpha_{\text{SAM}} \) was \( 10^{-1} \). (We reported the STM surface profiles of two different regions of the sample in Figure S4.)

Estimation of the Effective Resistivity of the \( \text{Ga}_2\text{O}_3 \) Layer. Because the surface of HOPG is flat and smooth, for the HOPG/\( \text{Ga}_2\text{O}_3/\text{EGaIn} \) junction \( \alpha_{\text{geo}} = \alpha_{\text{elec}} = \alpha_{\text{tip}} \). We used this value of the ratio \( \alpha_{\text{elec}}/\alpha_{\text{geo}} = \alpha_{\text{tip}} = 10^{-1} \) to estimate the value of the effective resistivity of the \( \text{Ga}_2\text{O}_3 \) layer as \( R_{\text{Ga}_2\text{O}_3} = 10^{-7} \Omega \cdot \text{cm}^2 \). This value of \( R_{\text{Ga}_2\text{O}_3} \) leads to a value of the resistivity of the \( \text{Ga}_2\text{O}_3 \) layer of \( \rho_{\text{Ga}_2\text{O}_3} = 1 \Omega \cdot \text{cm} \) when we consider an average thickness of this layer of \( \sim 1 \text{ nm} \).\(^{41} \) (The bulk resistivity of EGaIn is \( \rho_{\text{Ga}_2\text{O}_3}/\text{EGaIn} = 2.9 \times 10^{-5} \Omega \cdot \text{cm} \).\(^{53} \)

Some aspects of our procedure, however, might lead to an overestimation of \( \rho_{\text{Ga}_2\text{O}_3} \) because the resistance of the HOPG/\( \text{Ga}_2\text{O}_3/\text{EGaIn} \) junction might contain contributions from the contact resistance, and because the oxide layer of a conical tip is certainly thicker than 1 nm, at least in some areas. The contact resistance (often called constriction resistance) is a geometrical effect determined by the shapes of microcontacts, and not by their areas\(^1,2,4,5,9 \) (for example, the contact resistance of a circular spot is determined by its radius). A much more accurate estimation of the current of the \( \text{Ga}_2\text{O}_3 \) layer than that we provided here would require the estimation of the number, per unit area, of these microcontacts, and the determination of their shapes.

In a previous study\(^41 \) we have shown that \( \sim 1 \text{ nm} \) is the average thickness of the \( \text{Ga}_2\text{O}_3 \) layer on a unstressed droplet of EGaIn. The mechanical manipulation, however, of an EGaIn droplet during the fabrication of a conical tip produces an accumulation of the oxide at the tip apex. It is certain that the thickness of this oxide layer is nonuniform over the whole contact area.

Correction for effective contact area yields \( J_0 \approx 10^{7.6 \pm 0.8} \text{ A/cm}^2 \). Using, in eq 5, values obtained for the fractions of the surface available for contact respectively for \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) conical tips ( \( \alpha_{\text{tip}} = 10^{-3} \)) and for \( \text{Ag}^{18} \)-SAM substrates ( \( \alpha_{\text{SAM}} = 10^{-1} \)), for junctions having structure \( \text{Ag}^{18} \)-SAM//\( \text{Ga}_2\text{O}_3/\text{EGaIn} \) using flattened conical tips, we estimated that the effective electrical contact area is approximately \( A_{\text{elec}} = 10^{-4} \Omega^{-0.5} \alpha_{\text{geo}} \). The correction of the experimental value of \( \langle |I_{d}| \rangle \) (Figure 1) for the effective electrical contact area provided an estimate for the injection current density of \( \langle \log |I_{d}| \rangle = 7.6 \pm 0.8 \text{ (A/cm}^2 \)). This corrected value of \( J_0 \) was compatible with those estimated for single-molecules approaches\(^3,5 \) and with those reported for large-area junctions using graphene\(^{11} \) and evaporated-Au\(^{12} \) top-electrodes used for SAMs formed on flat substrates (Figure 8; we marked as “\( \text{Ga}_2\text{O}_3/\text{EGaIn corrected (estimate)} \)” the value of \( \langle |I_{d}| \rangle \) corrected for the estimated value of the effective electrical contact area).

**Conclusion**

\( \text{Ga}_2\text{O}_3/\text{EGaIn-based} \) junctions show a reproducible value of the effective electrical contact area. In this paper, we have described a simple technique for the fabrication of what we call “flattened” \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) conical tips. Using these tips reduced the variability in values of \( \log |I_{d}| \) from \( \log |I_{d}| = 0.5 \pm 1.1 \) for as-fabricated tips to \( \log |I_{d}| = 0.3 \). The procedure used to flatten the conical tips also retained the convenience of using conical EGaIn top-electrodes.

The comparison of the electrical behavior of smooth Hg-drop top-electrodes with that of flattened (but intrinsically rough) \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) conical tips suggests, in junctions having structure \( \text{Ag}^{18} \)-SAM//\( \text{Ga}_2\text{O}_3/\text{EGaIn} \), the effective electrical contact area is \( A_{\text{elec}} = 10^{-4} \Omega^{-0.5} \alpha_{\text{geo}} \), where \( \alpha_{\text{geo}} \) is the geometrical contact area measured by optical microscopy. This value of \( A_{\text{elec}} \)—a value that is small, but compatible with estimates of the area of physical contact from measurements of adhesion and friction between surfaces\(^21-27 \)—was reproducible from junction to junction. The high reproducibility may perhaps surprise, but it is plausibly attributable to the low compressibility of the SAM, and to the (roughly) constant load applied to the contact. Once a stable contact is formed on top of the SAM (using the observable wrinkling of the tip apex as an intrinsic sensor of the load applied to the junctions), the load applied to the contact cannot be significantly further varied: pushing the \( \text{Ga}_2\text{O}_3/\text{EGaIn} \) conical tip against the substrate simply deforms the tip (by making it bulge laterally), and increases (perhaps slightly) the geometrical contact area. We can also infer that following the same procedure for the fabrication of different tips gives surfaces of the \( \text{Ga}_2\text{O}_3 \) layer.
with a reproducible roughness. We believe that the reproducibility of the roughness of the Ga2O3 layer and the invariance of the load applied to the SAM//Ga2O3/EGaIn contacts result in reproducible values of $A_{\text{elec}}/A_{\text{geo}}$.

For Ga2O3/EGaIn top-electrodes, the resistance of the oxide layer is not important. For junctions formed with flattened Ga2O3/EGaIn conical tips, we observed a linear variation of values of (log($f$)) with a constant slope ($\beta = 0.75 \pm 0.02 \text{ Å}^{-1}$; $\beta = 0.92 \pm 0.02 \text{nC}^{-1}$) for tunneling through SAMs of SC$_n$ in the range of lengths from $n=0$ to $n=18$. We would not observe this linearity over the complete range (values of current densities varied over 7 orders of magnitude) if the resistance of the Ga2O3 layer were contributing to the resistance of the junction.

We do not know, however, if this value of $\beta$ estimated from measurements of tunneling across AgTS-SC$_n$/Ga2O3/EGaIn junctions is the true value of $\beta$ characteristic for tunneling across n-alkanethiolates. Values of $\beta$ for tunneling through n-alkanethiolates vary by $\sim$20% across different methods (Figure 8); whether this range is due to true variations of the characteristics of SAMs of n-alkanethiolates (e.g., the orientation, order, and density of the packing of the chains, differences in the topography of the supporting metal electrode), or to artifacts characteristic of the different junctions, remains unresolved.

The consensus value of $J_0$ for tunneling through n-alkanethiolates lies in the range $10^{-2}$—$10^{-4} \text{ A·cm}^{-2}$ (at $V = +0.5 \text{ V}$). For junctions with structure AgTS-SC$_n$/Ga2O3/EGaIn (conical tips), converting the value of the geometrical contact area ($A_{\text{geo}}$) into the estimated value of the effective electric contact area ($A_{\text{elec}} = 10^{-4}0.05^3A_{\text{geo}}$) led to a value of the effective injection current density $J_0 = 10^{-3}0.08 \text{ A·cm}^{-2}$. This corrected value of $J_0$ is compatible with those obtained for junctions using smooth and flat electrodes, that is, junctions using electrodes that maximize the value of $A_{\text{elec}}/A_{\text{geo}}$. Junctions formed with Hg-drops on top of alkyl chains anchored to silicon surfaces yielded $J_0 = 10^{-5}0.5 \text{ A·cm}^{-2}$, whereas large-area junctions using flat metal substrates (RMS = 0.7 Å) and flat top-electrodes (e.g., graphene), or conformal, evaporated Au electrodes, yielded rates of charge transport with $J_0 = 10^8 \text{ A·cm}^{-2}$. These results consolidate a consensus value of the injection current for SAMs of n-alkanethiolates in the range $10^{-2}$—$10^{-4} \text{ A·cm}^{-2}$ ($V = +0.5 \text{ V}$) (Figure 8).

Values of $J_0$ are $10^6 \text{ A·cm}^{-2}$ (Figure 8, gray field) might imply an overestimation of the effective electrical contact area. In junctions using rough Ga2O3/EGaIn top-electrodes, or rough, as-evaporated metal substrates (and using Hg/polymer, or Hg-SAM top-electrodes), the assumption that $A_{\text{elec}} = A_{\text{geo}}$ leads to values of $J_0$ in the range $10^2$—$10^3 \text{ A·cm}^{-2}$. These low experimental values of $J_0$ cannot be rationalized by a hypothetical high resistance of the top-electrodes: Hg/polymer and Ga2O3/EGaIn are highly conductive materials. We believe that, due to the roughness of the electrodes, the value of $A_{\text{geo}}$ overestimates the effective electrical area of contact ($A_{\text{elec}}$) of these junctions, thus resulting in an underestimation of $J_0$.

The value $10^8 \text{ A·cm}^{-2}$ might be a hypothetical upper limit to possible experimental estimations of $J_0$ for SAMs of n-alkanethiolates. We estimated this value of $J_0$ by extrapolating the value of $J_0$ ($\sim 1 \times 10^{-5} \text{ A·mol}^{-1}$) measured for single n-alkanethiolates in STEM-based junctions (Figure 8) to the value of $J_0$ for the theoretical number of molecules per cm$^2$ of the SAM (on Au(111)), this number is $4.5 \times 10^{14} \text{ mol·cm}^{-2}$). This extrapolation assumes that the SAM is free of defects and has a homogeneous density of molecules, and that all the molecules of this ideal SAM are in contact with the top-electrode; these assumptions are unrealistic in experiments with large-area junctions, for which values of $J_0$ in the range $10^6$—$10^8 \text{ A·cm}^{-2}$ are more probable (Figure 8).

Comparing values of $J_0(V)$ across different methods will require the use of a common standard to take into account

---

**Figure 8.** Plot of values of $\beta$ versus values of log$J_0$ ($V = +0.5 \text{ V}$) reported (filled squares) or estimated (empty squares) for tunneling through n-alkanethiolates with junctions using top-electrodes indicated on the top axis. Numbering is from Table 1. The horizontal arrowed line points to the experimental value of $J_0$ for AgTS-SAM//Ga2O3/EGaIn corrected for the estimated value of the effective contact area ($A_{\text{elec}} = 10^{-4}0.05^3A_{\text{geo}}$); the horizontal error bar of this estimate incorporates the uncertainties on the estimation of $J_0$ from tunneling across SAMs, and on the estimation of the effective electrical contact area. Junctions grouped in the gray zone use either rough top-electrodes or rough bottom-electrodes.
differences in measured values of $J(V)$. The values of $A_{\text{elec}}/A_{\text{geo}}$ for these different techniques are unknown; in addition, a number of factors other than the value of the ratio $A_{\text{elec}}/A_{\text{geo}}$ might contribute to the variability of the values of $J_0$ within the consensus range; these parameters include the nature of the top- and bottom-contacts (e.g., covalent or van der Waals), the nature of the materials used as electrodes, and the presence of contaminants. We recommend using SAMs of SC$_{10}$ and SC$_{16}$ as standards for the calibration of values of $\beta$

The value of the effective electrical contact area is not important in physical-organic studies; its reproducibility is important. Using Ga$_2$O$_3$/EGaIn flattened conical tips as top-electrodes yielded a (roughly) constant value of the standard deviation (0.3) of the value of log$J$ across SAMs of individual $n$-alkanethiolates, and a value of the tunneling decay factor $\beta = 0.75 \pm 0.02$ Å$^{-1}$ (or $\beta = 0.92 \pm 0.02$ nC$^{-1}$) that falls in the 90% consensus range of values of $\beta$ estimated by different techniques (Figure 8). These results indicate that, in Ag$^{+}$-SAM/Ga$_2$O$_3$/EGaIn junctions, the value of $A_{\text{elec}}/A_{\text{geo}}$ is (surprisingly) reproducible from junction to junction, and that variations of measured values of tunneling currents across different SAMs are primarily due to differences in the lengths of the $n$-alkanethiolates. The dispersion in data collected with flattened Ga$_2$O$_3$/EGaIn conical tips was smaller than that observed for as-fabricated conical tips; flattening of the tips, however, had no effect on the mean values (i.e., $\langle \log J \rangle$) of the distributions of experimental values of log$J$.

**Ga$_2$O$_3$/EGaIn top-electrodes are a convenient methodology for physical-organic studies of charge tunneling**. Table 2 summarizes advantages and disadvantages that we identified for the most common techniques used for studying charge transport through molecules anchored to conductive

---

**Table 2. Summary of Advantages and Disadvantages of the Most Common Types of Molecular Junctions**

<table>
<thead>
<tr>
<th>top-electrode</th>
<th>advantages</th>
<th>disadvantages</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ga$_2$O$_3$/EGaIn</td>
<td>• rapid data collection</td>
<td>• surface roughness</td>
</tr>
<tr>
<td></td>
<td>• high yield (90%) of working junctions</td>
<td>• limited range of temperatures</td>
</tr>
<tr>
<td></td>
<td>• simple design</td>
<td>• limited range of voltages</td>
</tr>
<tr>
<td></td>
<td>• nondamaging contact</td>
<td>• subject to adventitious contaminations</td>
</tr>
<tr>
<td></td>
<td>• conformal contact</td>
<td></td>
</tr>
<tr>
<td></td>
<td>• insensitive to contact load</td>
<td></td>
</tr>
<tr>
<td></td>
<td>• for flattened tips, small dispersion in data for log$J$</td>
<td></td>
</tr>
<tr>
<td>Hg-Drops</td>
<td>• well-defined surface</td>
<td>• toxic</td>
</tr>
<tr>
<td></td>
<td>• rapid data collection</td>
<td>• volatile</td>
</tr>
<tr>
<td></td>
<td>• conformal contact</td>
<td>• amalgamates with Au and Ag</td>
</tr>
<tr>
<td></td>
<td>• nondamaging contact</td>
<td>• needs hexadecane bath</td>
</tr>
<tr>
<td></td>
<td>• insensitive to contact load</td>
<td>• surface contamination (high surface energy)</td>
</tr>
<tr>
<td>Hg-SAM</td>
<td>• rapid data collection</td>
<td>• toxic</td>
</tr>
<tr>
<td></td>
<td>• conformal contact</td>
<td>• amalgamates with Au and Ag</td>
</tr>
<tr>
<td></td>
<td>• nondamaging contact</td>
<td>• needs hexadecane bath</td>
</tr>
<tr>
<td></td>
<td>• insensitive to contact load</td>
<td>• intercalation of molecules from the top-SAM into the bottom-SAM might occur</td>
</tr>
<tr>
<td></td>
<td>• subject to adventitious contaminations</td>
<td>• possible lateral movement, or exchange of SAM on Hg</td>
</tr>
<tr>
<td>Graphene</td>
<td>• well-defined top-interface</td>
<td>• complicated experimental protocol</td>
</tr>
<tr>
<td></td>
<td>• high stability</td>
<td>• sensitive to load applied to contact</td>
</tr>
<tr>
<td></td>
<td>• high durability</td>
<td>• time consuming</td>
</tr>
<tr>
<td></td>
<td>• high yield</td>
<td></td>
</tr>
<tr>
<td></td>
<td>• resistant to a broad range of temperatures</td>
<td></td>
</tr>
<tr>
<td></td>
<td>• usable at high voltages</td>
<td></td>
</tr>
<tr>
<td>Single Molecules</td>
<td>• rapid collection of data</td>
<td>• unknown number of contacted molecules</td>
</tr>
<tr>
<td>(STM, AFM)</td>
<td>• resistant to a broad range of temperatures</td>
<td>• complicated experimental protocol</td>
</tr>
<tr>
<td></td>
<td>• usable at high voltages</td>
<td>• time consuming</td>
</tr>
<tr>
<td></td>
<td>• high yield</td>
<td>• high equipment cost</td>
</tr>
<tr>
<td></td>
<td>• resistant to a broad range of temperatures</td>
<td>• sensitive to contact load</td>
</tr>
<tr>
<td></td>
<td>• usable at high voltages</td>
<td></td>
</tr>
<tr>
<td>Conductive Polymers</td>
<td>• durability</td>
<td>• requires thermal annealing that can damage the SAM</td>
</tr>
<tr>
<td></td>
<td>• high durability</td>
<td>• complicated design</td>
</tr>
<tr>
<td></td>
<td>• high yield</td>
<td>• possible intercalation of molecules into the SAM</td>
</tr>
<tr>
<td></td>
<td>• resistant to a broad range of temperatures</td>
<td>• sensitive to load</td>
</tr>
<tr>
<td></td>
<td>• usable at high voltages</td>
<td>• time consuming</td>
</tr>
<tr>
<td>Evaporated Au</td>
<td>• conformal contact</td>
<td>• damaging contact</td>
</tr>
<tr>
<td></td>
<td>• high yield</td>
<td>• formation of filaments</td>
</tr>
<tr>
<td></td>
<td>• resistant to a broad range of temperatures</td>
<td>• dilute experimental protocol</td>
</tr>
<tr>
<td></td>
<td>• usable at high voltages</td>
<td>• time consuming</td>
</tr>
</tbody>
</table>

**Table 2. Summary of Advantages and Disadvantages of the Most Common Types of Molecular Junctions**
substrates. From this comparison, Ga₂O₃/EGaIn top-electrodes emerge as a particularly convenient technology for physical-organic studies of charge transport through molecules. Physical-organic approaches, which examine only trends in \( J(V) \) as a function of the structure of the molecules making up the SAM, require that the properties of the top- and bottom-interfaces of these different types of junction are unchanged across a series of measurements. The roughness of the Ga₂O₃ layer gives an uncertain morphology to the SAM/Ga₂O₃ interface, but, so long as the properties of this interface remain constant, physical-organic protocols can be applied to the study of charge transport through SAMs, even though the SAM/Ga₂O₃ interface is not well defined. (None of the interfaces of the methods listed in Table 2 is, however, entirely defined.)

The simplicity and rapidity in assembling junctions using Ga₂O₃/EGaIn top-electrodes that make it possible to collect large numbers of data (\( \sim 10^3 \) per day) are currently unmatched by any other method listed in Table 2. We stress that collection of large numbers of data is critical to validating the statistical significance of studies of structure–tunneling relationships by physical-organic protocols.

**Ga₂O₃/EGaIn tips do not damage the SAM.** Ga₂O₃/EGaIn top-electrodes enable a rapid collection of data because they do not require a fine control of the load to form nondamaging contacts on top of the SAM. The load applied to contacts using soft Ga₂O₃/EGaIn conical tips—or liquid metal electrodes in general—cannot be significantly varied; pushing the Ga₂O₃/EGaIn electrode against the sample simply increases the geometrical contact area of the junction. By contrast, small variations of the load applied to junctions using solid top-electrodes might change the effective electrical contact area, deform the SAM, and even damage the SAM. With only the exception of Hg-based junctions, all other methods listed in Table 2 use solid top-electrodes; the loads applied to these contacts, however, have never been reported.

**Ga₂O₃/EGaIn is an affordable technology that might allow comparison of results obtained in different laboratories.** Several years of work in our laboratory have proved that EGaIn-based junctions are a practical and convenient methodology for physical-organic studies of charge tunneling through SAMs.

So far, the effect of the resistance of the Ga₂O₃ layer on the electrical behavior of the junctions, and the value of the effective electrical contact area between SAMs and Ga₂O₃/EGaIn conical tips, have been two major unresolved issues in the interpretation of data obtained with EGaIn-based junctions. In this paper we have shown that the resistance of the Ga₂O₃ layer is not important, and that the effective electrical contact area—which is \( \sim 10^{-4} \) the geometrical contact area—is reproducible across different experiments; the correction of current densities for this value of the effective electrical contact area led to results for tunneling across n-alkanethiolates compatible with those reported for techniques far more complex and expensive than Ga₂O₃/EGaIn electrodes.

Using Ga₂O₃/EGaIn top-electrodes still requires attention to experimental details (especially the fabrication of the conical tips), but the procedure needs only a few days to learn. The simple (and inexpensive) fabrication of EGaIn-based junctions can be replicated in any laboratory, and the availability of very well-defined reference data (such those of Figure 1) for comparison, calibration, and use as standards makes comparisons among data generated in different laboratories straightforward.